

Notice of References Cited		Application/Control No.	Applicant(s)/Patent Under Reexamination LEE, SUK HUN	
		Examiner Brian Kunzer	Art Unit 2814	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6,266,355 B1	07-2001	Sverdlov, Boris N.	372/45.01
*	B	US-6,479,836 B1	11-2002	Suzuki et al.	257/15
*	C	US-6,608,330 B1	08-2003	Yamada, Motokazu	257/90
*	D	US-6,664,560 B2	12-2003	Emerson et al.	257/14
*	E	US-6,657,234 B1	12-2003	Tanizawa, Koji	257/79
*	F	US-6,720,570 B2	04-2004	Lee et al.	257/14
*	G	US-6,830,948 B2	12-2004	Koike et al.	438/46
*	H	US-6,958,497 B2	10-2005	Emerson et al.	257/94
*	I	US-6,838,705 B1	01-2005	Tanizawa, Koji	257/101
*	J	US-6,849,864 B2	02-2005	Nagahama et al.	257/22
*	K	US-6,906,352 B2	06-2005	Edmond et al.	257/94
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages
	U	X.H. Zheng, "Effects of TMIn flow rate of barrier layer on the optical and structural properties of In _x Ga _{1-x} N/In _y Ga _{1-y} N multiple quantum wells" Journal of Crystal Growth, Volume 257, Issues 3-4, October 2003 (received May 26, 2003), Pages 326-332
	V	S. Keller, "Growth and Properties of InGaN nanoscale islands on GaN" Journal of Crystal Growth, Volumes 189-190, 15 June 1998, Pages 29-32
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.